

EV372468604

DECLARATION OF JOINT INVENTORS FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled "Methods of Depositing Silicon Dioxide Comprising Layers in the Fabrication of Integrated Circuitry, Methods of Forming Trench Isolation, and Methods of Forming Arrays of Memory Cells", Serial No. 10/806,923, filed March 22, 2004. I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.

PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such

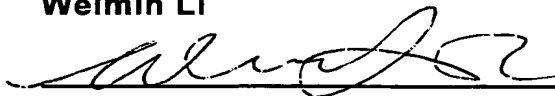
willful false statement may jeopardize the validity of the application or any patent issued therefrom.

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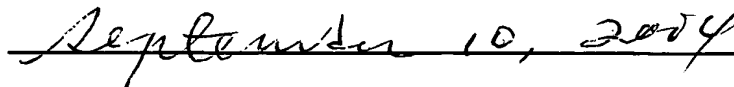
Full name of inventor:

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Inventor's Signature:



Date:



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